# UNISONIC TECHNOLOGIES CO., LTD

# UTG50N120-G2

**Preliminary** 

Insulated Gate Bipolar Transistor

TO-247

# 1200V TRENCH GATE FIELD-STOP IGBT

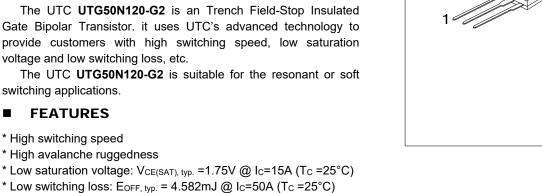
#### DESCRIPTION

Gate Bipolar Transistor, it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

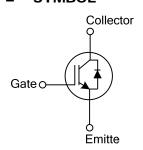
The UTC UTG50N120-G2 is suitable for the resonant or soft switching applications.

#### **FEATURES**

- \* High switching speed
- \* High avalanche ruggedness
- \* Low switching loss:  $E_{OFF, typ.} = 4.582 \text{mJ} @ I_C = 50 \text{A} (T_C = 25 ^{\circ}\text{C})$

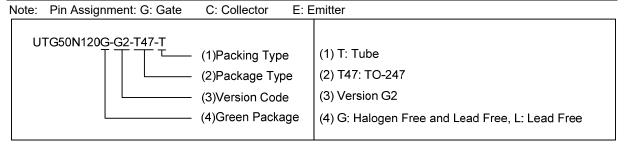


#### **SYMBOL**

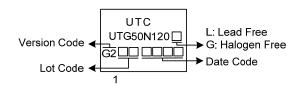


#### ORDERING INFORMATION

Ordering Number		Daalsana	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG50N120L-G2-T47-T	UTG50N120G-G2-T47-T	TO-247	G	С	Е	Tube	



### **MARKING**



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## **■ ABSOLUTE MAXIMUM RATINGS**

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		Vces	1200	V
Gate-Emitter Voltage		V <sub>GES</sub>	±20	V
Continuous Collector Current	T <sub>C</sub> =25°C	- Ic	100	Α
	T <sub>C</sub> =100°C		50	Α
Collector Current Pulsed (Note 1)		Ісм	200	Α
Diode Forward Current	T <sub>C</sub> =25°C	lF	100	Α
	T <sub>C</sub> =100°C		50	Α
Short Circuit Withstand Time				
$V_{GE} = 15V, V_{CC} \le 200V$		tsc		μs
Allowed number of short circuits < 1000			10	
Time between short circuits: ≥1.0s				
<i>T</i> <sub>VJ</sub> = 25°C				
Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	285	W
Operating Junction Temperature		TJ	-40 ~ +150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

## **■ THERMAL DATA**

PARAMETER	SYMBOL	RATING	UNIT	
Junction to Case	θ <sub>JC</sub>	0.44	°C/W	

# ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
Off Characteristics				ı				
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>		1200			V		
Collector Cut-Off Current	Ices	V <sub>CE</sub> =V <sub>CES</sub> , V <sub>GE</sub> =0V			5	μA		
G-E Leakage Current	Iges	V <sub>GE</sub> =V <sub>GES</sub> , V <sub>CE</sub> = 0V			±100	nA		
On Characteristics								
Gate to Emitter Threshold Voltage	V <sub>GE(TH)</sub>	Ic=250μA, VcE=V <sub>GE</sub>	4.5		7.5	V		
Collector to Emitter Saturation Voltage	\/	Ic=50A, V <sub>GE</sub> =15V		1.75	2.1	V		
	V <sub>CE(SAT)</sub>	I <sub>C</sub> =50A, V <sub>GE</sub> =15V, T <sub>C</sub> =125°C		2.1		V		
Dynamic Characteristics								
Input Capacitance	CIES			2640		pF		
Output Capacitance	Coes	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz		134.6		pF		
Reverse Transfer Capacitance	Cres			70		pF		
Switching Characteristics								
Total Gate Charge	Q <sub>G</sub>			213.6		nC		
Gate-Emitter Charge	Q <sub>GE</sub>	V <sub>CE</sub> =600V, I <sub>C</sub> =50A, V <sub>GE</sub> =15V		20		nC		
Gate-Collector Charge	Q <sub>GC</sub>			133.4		nC		
Turn-On Delay Time	t <sub>DON)</sub>			17		ns		
Rise Time	t <sub>R</sub>			24		ns		
Turn-Off Delay Time	t <sub>DOFF)</sub>	Vcc=600V, Ic=50A, Rg=5Ω,		260		ns		
Fall Time	t⊧	V <sub>GE</sub> =0∼15V, L=500uH		213		ns		
Turn-On Switching Loss	Eon			4.29		mJ		
Turn-Off Switching Loss	Eoff			4.582		mJ		
SOURCE- DRAIN DIODE RATINGS AN	D CHARACTE	RISTICS						
Forward Voltage Drop	V <sub>FM</sub>	I <sub>F</sub> =50A			3.0	V		
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =50A,		73.7		ns		
Reverse Recovery Charge	Qrr	dl/dt=100A/µS		2.2		μC		

<sup>2.</sup> Pulse width limited by maximum junction temperature.

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